

BUK7606-55B

N-channel TrenchMOS standard level FET Rev. 02 — 21 June 2010

Product data sheet

Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids



1.4 Quick reference data

Table 1. Quick reference data

Doromotor	Conditions		Min	Tvn	Mov	Linit
Parameter	Conditions		IVIII	тур	iviax	Unit
drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	-	55	V
drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u>	-	-	75	Α
total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	254	W
racteristics						
drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>		-	5.1	6	mΩ
ruggedness						
non-repetitive drain-source avalanche energy	I_D = 75 A; $V_{sup} \le$ 55 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	680	mJ
characteristics						
gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 44 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 13		-	19	-	nC
	voltage drain current total power dissipation racteristics drain-source on-state resistance rruggedness non-repetitive drain-source avalanche energy	drain-source voltage $ T_{j} \geq 25 \text{ °C}; T_{j} \leq 175 \text{ °C} $ voltage $ T_{gS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; $ see Figure 1; see Figure 3 $ T_{mb} = 25 \text{ °C}; $ see Figure 2 $ T_{mb} = 25 \text{ °C}; $ see Figure 2 $ T_{mb} = 25 \text{ °C}; $ see Figure 2 $ T_{mb} = 25 \text{ °C}; $ see Figure 2 $ T_{mb} = 25 \text{ °C}; $ see Figure 12 $ T_{j} = 25 \text{ °C}; $ see Figure 11; see Figure 12 $ T_{j} = 25 \text{ °C}; $ see Figure 12 $ T_{j} = 25 \text{ °C}; $ see Figure 12 $ T_{j} = 25 \text{ °C}; $ see Figure 12 $ T_{j} = 25 \text{ °C}; $ see Figure 12 $ T_{j} = 25 \text{ °C}; $ see Figure 12 $ T_{j} = 25 \text{ °C}; $ see Figure 12 $ T_{j} = 25 \text{ °C}; $ see Figure 12 $ T_{j} = 25 \text{ °C}; $ see Figure 12 $ T_{j} = 25 \text{ °C}; $ see Figure 12 $ T_{j} = 25 \text{ °C}; $ see Figure 12 $ T_{j} = 25 \text{ °C}; 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I_{D} = 25 \text{A}; \qquad - \\ \text{on-state} \qquad T_{j} = 25 ^{\circ}\text{C}; \\ \text{resistance} \qquad \text{see } \frac{\text{Figure 11}}{\text{see Figure 12}}; \text{see } \frac{\text{Figure 12}}{\text{see Figure 12}}$ Pruggedness $\text{non-repetitive} \qquad I_{D} = 75 \text{A}; V_{sup} \leq 55 \text{V}; \qquad - \\ \text{drain-source} \qquad R_{GS} = 50 \Omega; V_{GS} = 10 \text{V}; \qquad - \\ \text{drain-source} \qquad \text{avalanche energy}$ $\text{T}_{j(init)} = 25 ^{\circ}\text{C}; \text{unclamped}$ Sharacteristics $\text{gate-drain charge} \qquad V_{GS} = 10 \text{V}; I_{D} = 25 \text{A}; \qquad - \\ V_{DS} = 44 \text{V}; T_{j} = 25 ^{\circ}\text{C};$	drain-source voltage $T_{j} \geq 25 \text{ °C}; T_{j} \leq 175 \text{ °C} \qquad - \qquad $	drain-source voltage $T_{j} \geq 25 ^{\circ}\text{C}; T_{j} \leq 175 ^{\circ}\text{C} \qquad - \qquad - \qquad 55$ drain current $V_{GS} = 10 \text{V}; T_{mb} = 25 ^{\circ}\text{C}; \qquad [1] \qquad - \qquad - \qquad 75$ see Figure 1; see Figure 3 $\text{total power dissipation}$ $T_{mb} = 25 ^{\circ}\text{C}; \text{see Figure 2} \qquad - \qquad - \qquad 254$ drain-source on-state $T_{j} = 25 ^{\circ}\text{C}; \text{see Figure 12}$ drain-source see Figure 11; see Figure 12 Fruggedness non-repetitive drain-source avalanche energy $T_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{unclamped}$ sharacteristics $T_{j} = 25 ^{\circ}\text{C}; \text{unclamped}$ sharacteristics $T_{j} = 25 ^{\circ}\text{C}; \text{unclamped}$ sharacteristics $T_{j} = 25 ^{\circ}\text{C}; \text{unclamped}$

^[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain[1]	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

^[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package	Package					
	Name	Description	Version				
BUK7606-55B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404				

BUK7606-55B

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4. Limiting values

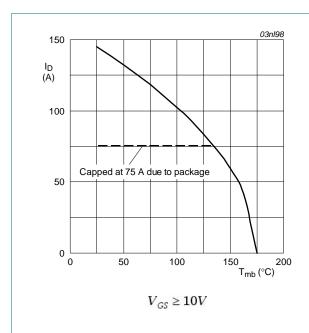
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	-	55	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	55	V
V_{GS}	gate-source voltage			-20	-	20	V
l _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 3</u> ; see <u>Figure 1</u>	<u>[1]</u>	-	-	145	Α
		$T_{mb} = 100 ^{\circ}\text{C}; V_{GS} = 10 \text{V}; \text{see} \frac{\text{Figure 1}}{}$	[2]	-	-	75	Α
		T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	[2]	-	-	75	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; $t_p \le 10 \mu s$; pulsed; see Figure 3		-	-	582	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	254	W
T _{stg}	storage temperature			-55	-	175	°C
Tj	junction temperature			-55	-	175	°C
Source-drain	diode						
I _S	source current	$T_{mb} = 25 ^{\circ}C$	<u>[1]</u>	-	-	145	Α
			[2]	-	-	75	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	-	582	Α
Avalanche ru	ggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 75 \text{ A; } V_{sup} \leq 55 \text{ V; } R_{GS} = 50 \Omega; \\ V_{GS} &= 10 \text{ V; } T_{j(init)} = 25 ^{\circ}\text{C; } unclamped \end{split}$		-	-	680	mJ
E _{DS(AL)} S	drain-source			-	-	680)

^[1] Current is limited by power dissipation chip rating.

^[2] Continuous current is limited by package.



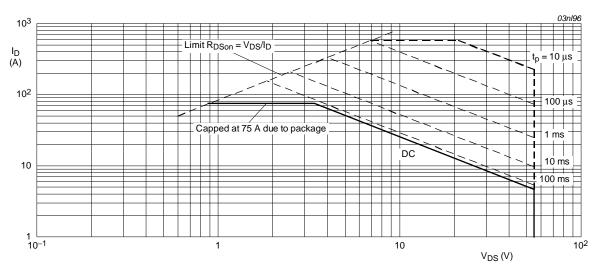
Pder (%)

80

40 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$

Fig 1. Normalized continuous drain current as a function of mounting base temperature

Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25$ °C; I_{DM} is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	-	0.59	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	-	50	K/W

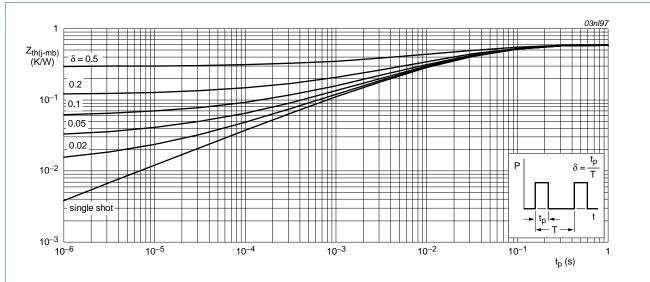


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

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BUK7606-55B

Characteristics

Table 6. **Characteristics**

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; see <u>Figure 10</u>	-	-	4.4	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; see <u>Figure 10</u>	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 10	1	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I _{GSS}	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 °C;$ see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	12	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	5.1	6	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$	-	64	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; see <u>Figure 13</u>	-	14	-	nC
Q_{GD}	gate-drain charge		-	19	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	3825	5100	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	783	940	pF
C _{rss}	reverse transfer capacitance		-	235	322	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω ; V_{GS} = 10 V; $R_{G(ext)}$ = 10 Ω ; T_j = 25 °C	-	30	-	ns
t _r	rise time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V}; R_{G(ext)} = 10 \Omega; T_j = 30 \text{ °C}$	-	46	-	ns
t _{d(off)}	turn-off delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	85	-	ns
t _f	fall time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C$	-	39	-	ns
L _D	internal drain inductance	from drain lead 6 mm from package to centre of die; $T_j = 25 ^{\circ}\text{C}$	-	4.5	-	nΗ
		from upper edge of drain mounting base to centre of die; $T_j = 25 ^{\circ}\text{C}$	-	2.5	-	nΗ
L _S	internal source inductance	from source lead to source bond pad; $T_j = 25 ^{\circ}\text{C}$	-	7.5	-	nΗ
Source-di	rain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 15	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	73	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	82	-	nC

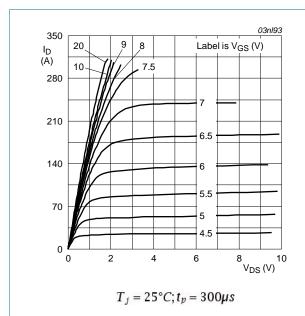


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

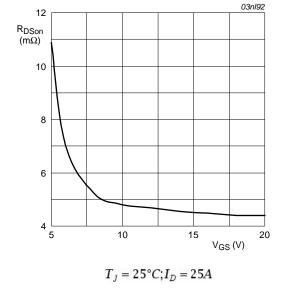


Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

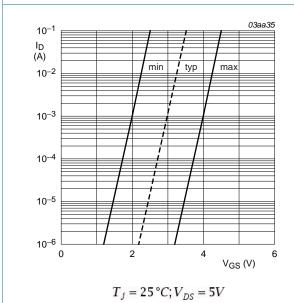


Fig 7. Sub-threshold drain current as a function of gate-source voltage

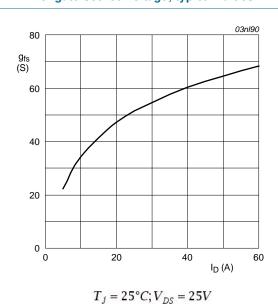


Fig 8. Forward transconductance as a function of drain current; typical values

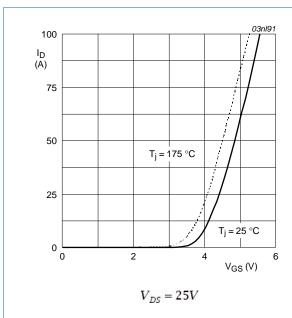


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

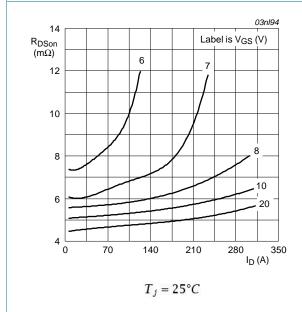
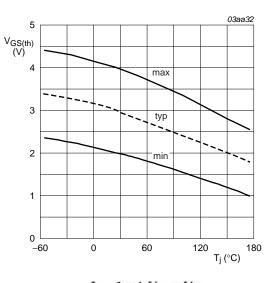


Fig 11. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 1 mA; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature

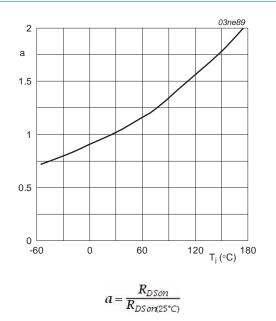


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

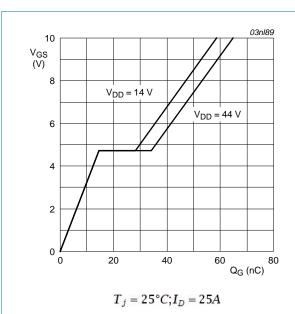
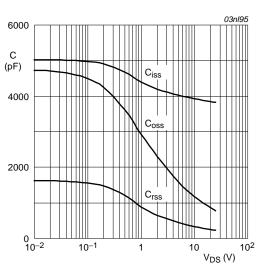


Fig 13. Gate-source voltage as a function of turn-on gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

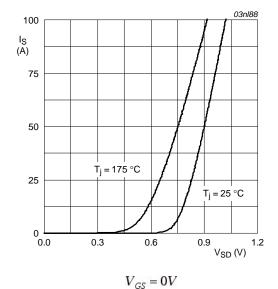


Fig 15. Source current as a function of source-drain voltage; typical values

7. Package outline

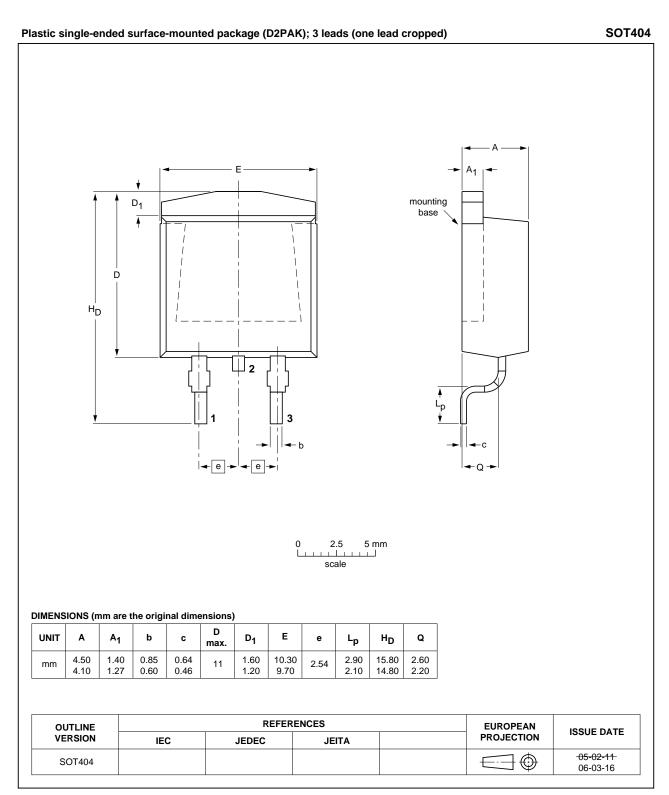


Fig 16. Package outline SOT404 (D2PAK)

N-channel TrenchMOS standard level FET

Revision history

Table 7. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7606-55B v.2	20100621	Product data sheet	-	BUK75_7606_55B v.1
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity of NXP Semiconductors. 			
	 Legal texts 	have been adapted to the	e new company name wh	ere appropriate.
	 Type numb 	er BUK7606-55B separat	ed from data sheet BUK7	75_7606_55B v.1.
BUK75_7606_55B v.1	20030331	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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